## Session II

## Poster Title: Analysis of Maximum Voltage Droops In Power Delivery Network

Student(s): Seunghyup Han Faculty: Prof. Madhavan Swaminathan

□ Objective:

- Effectively estimate voltage droops and clarify the causes
- Estimate voltage droops from arbitrary currents
- □ Technical Approach:
  - Use the simplified equation and full equation derived in previous work
  - Apply the decreased envelop term caused by current rise time
- Latest Results:
  - Estimation of voltage droops from a step current considering its rise time
  - Estimation voltage droops when multiple impedance peaks existed





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## Session II: Impedance Response Extrapolation of PDNs using Recurrent Neural Networks Student: Osama Wagar Bhatti Faculty: Madhavan Swaminathan



- Objective:
  - Design Machine Learning architectures that aid in design of power delivery networks reducing design time and computational complexity
- Technical Approach:
  - Deep neural networks provide ways to generate responses directly from physical structure of the circuit
  - Correlation in frequency space enables us to form connections to build impedance response
- ❑ Latest Results:
  - PDN impedance response can be extrapolated
  - 66% bandwidth extension achieved with 0.004 MSE ohm squared
  - Computation time





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## Session II - Embedded inductors and Power Stage Co-Design for 48V to 1V Integrated Voltage Regulators

Student(s): Claudio Alvarez, Srinidhi Suresh, Venkatesh Avula Faculty: Dr. Himani Sharma, Dr. Raj Pulugurtha, Prof. Madhavan Swaminathan, Prof. Rao Tummala

## **Objective:**

- Design and demonstrate a 48V to 1V IVR with embedded inductors
- IVR Efficiency 90% (Power Stage 95%, Inductor 95%)
- **Technical Approach:** 
  - Power stage and inductor co-design
  - Frequency and duty cycle dependency on inductor efficiency
- Latest Results:

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- Determination of the minimum inductor requirements for 95% efficiency
- Design of a high performance toroidal structure on magnetic sheets
- Development of the fabrication process



NGaN

 $C_{in}$ 

Magnetic

Sheet

Efficiency % 6.0 %

0.85

Frequency MIHz 15

NGaN

Inductor Efficiency with L = 100 nH

5 0

 $C_{out}$ 



0.15

0.1

0.05

This work was supported in part by the Georgia Tech PRC industry consortium members. This work was supported in part by the Semiconductor Research Corporation (SRC) and DARPA.



Power Stage

Copper Layers

ubstrate

Session 2Poster Title: Ultra-High Efficiency Substrate-Embedded Inductors for IVRsStudent: Srinidhi SureshFaculty: Dr. Himani Sharma, Prof. R. Tummala, Prof. M. Swaminathan

- **Objective:** 
  - Miniaturized high-density, ultra-low DC resistance embedded inductors for low (1 10 MHz) and high frequency (100 -140 MHz) IVRs.
- **Technical Approach:** 
  - Spiral (2D), solenoid and toroid (3D) inductor topologies are modeled and fabricated to realize substrate-embedded inductors.
  - Advanced metal-polymer composites are used as the substrate core material.
- □ Latest Results:
  - Optimized 2D inductors fabricated using low and high frequency composite materials.
  - Fabricated solenoid inductors using low and high frequency composite materials (to be measured).
  - Modeled novel toroid inductors with an efficiency ~96% and established process flow (being optimized).







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Session II: **Thermal Analysis of Integrated Voltage Regulators** Students: Venkatesh Avula, Lydia Mele and Claudio Alvarez Faculties: Dr. Vanessa Smet, Prof. Madhavan Swaminathan and Prof. Yogendra Joshi

- Objective:
  - Model, design and demonstrate substrate-integrated cooling solutions for 48V-1V IVR modules with embedded inductors.
- □ Technical Approach:
  - Board- or package-integrated vapor chamber as a thermal solution for the IVR, in combination with forced air cooling.
- Latest Results:

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- System-level thermal impact of integrated voltage regulators.
- Thermal analysis of two heterogenous integration architectures of IVR.

			Heatsink		
5	<b>↓</b> 95.5514 C	Heat spreader	105 962 C	IVR dielet	
		CPU SOC dielet		Embedded inductors	Package
Package					
PC	B				

Temperature profile of a package-on-package IVR configuration

\* This work was supported in part by ASCENT, one of six centers in JUMP, a Semiconductor Research Corporation (SRC) program sponsored by DARPA.



for next-generation Electric Vehicle Drivetrains

Mickael Mauger, Prasad Kandula and Deepak Divan

Session II: Soft-Switching Current Source Inverter

Objective:

- Develop new power electronics for high power density, high efficiency and high reliability electric vehicle drivetrains
- **Technical Approach**:
  - Use novel soft-switching current source topology integrating all required functionalities into a single conversion stage
  - Leverage latest SiC devices advancements with controlled dv/dt

Latest Results:

 Unprecedented efficiency profile well-suited for electric vehicle applications







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# Session 2 – Design & Demonstration of 3D Stacked Rectifier Module

Student: Haksun Lee

Faculties: Dr. Vanessa Smet, Prof. Rao Tummala



□ Objective: Design, demonstrate and characterize a new class of ultra-low parasitics, 3D SiC power modules with high efficiency, high dv/dt capability, and enhanced thermal Management and thermomechanical reliability

## Technical Approach:

- Minimized parasitics L&C through 3D stacking suitable for high speed switching
- Thick metal structures for high thermal capacitance, double-sided large area interconnect
- Highly modular (ease of scalability to higher power)
- Compatible with current and future manufacturing processes

## Latest Results:

- Design and demonstration of 200V/15A 3D full-bridge rectifier module
- Electrical and thermal characterization of the module



Session II - Bayesian Learning for Optimization and Analysis of SiC-based Inverter Package

Student(s): Hakki M. Torun, Ryan Wong Faculty: Dr. Vanessa Smet, Prof. Madhavan Swaminathan

- Objective:
  - Determine optimal geometry of power card to maximize thermal performance, focusing on degrees of freedom in Z-direction as a first step.
  - Quantify which parameters affect the package temperature the most.
- □ Technical Approach:
  - Bayesian Active Learning to ensure convergence to global optima while minimizing CPU time & establish confidence bounds on the predictions.
  - ☐ Latest Results:
    - □ Critical parameters are identified.
    - □ Improved thermal performance (~2°C)







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**PRC IAB Meeting** 



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## Session 2 | Multiphysics Modeling of SiC-Based Power Inverters in (H)EVS: Integrated Cooling

Students: Ryan Wong, Lydia Mele, Hakki Torun Faculties: Dr. Vanessa Smet, Prof. Antonia Antoniou, Prof. Yogendra Joshi, Prof. Madhavan Swaminathan

#### **Objective:**

- Model, design, and demonstrate integrated single-phase cooling solutions for SiC 3D lead frame-based power cards.
- **Technical Approach:** 
  - Use of machine learning algorithms to optimize wick structures in the auto-generation and combination of different layout, geometries, and materials.
- Latest Results:
  - Established framework for multiphysics environment and machine learning, with material development underway.



Advanced Cold Plates as Current Terminals



**Direct Chip Cooling with Liquid Dielectric** 

 Use of semi-/fully-additive manufacturing for design flexibility

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Session II – High Temperature, High Voltage and High Thermal Epoxy Molding Compound Student(s): Jiaxiong Li Faculty: Prof. CP Wong

□ Objective:

- Demonstrate novel EMC with high temperature and high voltage reliability
- Design filler technology to enable high thermal conductivity
- □ Technical Approach:
  - Incorporation of high temperature resin (cyanate ester) in epoxy
  - Design high thermal filler (BN) stacking structure and surface chemistry
  - Synthesis of high purity low moisture absorption resin and utilize additives (ion and electron trap) to improve BDV

□ Latest Results:

- Analysis of high temperature aging on Tg and chemical structure of CE/EP
- Synthesis of BN coated SiO2 from self-assembly





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## Session # 2, Sintered Nanoporous Copper Die-Attach Interconnections for High-Power, High-Temperature Applications

Students: Kashyap Mohan, Ramon Sosa Faculty: Prof. Antonia Antoniou, Dr. Vanessa Smet, Prof. Rao Tummala

• Objective:

Design and demonstrate low-cost, all-Cu die-attach interconnections with enhanced processability, by low-temperature (<250°C), low-pressure (<5MPa) sintering, for superior electrical, thermal and reliability performances under high operating temperatures (>250°C) and power densities.

- **Technical Approach:** 
  - PRC is developing all-copper die-attach technology based on low-temperature film sintering of nanoporous copper (np-Cu), as an alternative to solders and Ag sintering.
  - · Sintering of np-Cu offers several over sintered Ag pastes
    - o No residual organics after sintering.
    - $\circ~$  Low shrinkage during assembly.
    - o Low-modulus of np-Cu helps in accommodating surface roughness during assembly.
    - High densification giving bulk-Cu like joint properties.
    - Industry standard SAP processing for fabrication.
    - Versatility in implementation- can be used as an insert or fabricated directly on substrates/wafers.

### Latest Results:

- Fabrication of np-Cu films complete.
- Work on sintering and assembly using np-Cu ongoing.



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## Session 2 – Poster Title: Additive Manufactured Foams for Power Electronics Thermal Management Faculty: Prof. Yogendra Joshi **Student:** Justin Broughton

Objective:

- Demonstrate AM foam structures for power electronics cooling
- Compare performance with commercial structures
- □ Technical Approach:
  - Numerical (CFD-HT) simulations with experimental validation
  - Pore-scale level models
- Latest Results:
  - Tortuosity was numerically compared for AM and traditional structures
  - Impact of attachment layer thermal conductivity investigated
  - Interfacial heat transfer coefficients compared to correlations









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Session II Poster Title: Feasibility of integrated single-stage 48V to 1V conversion using GaN power devices Student: Minxiang Gong Faculty: Arijit Raychowdhury

Objective:

- Integrated single-stage 48V to 1V voltage regulator for point-of-load
- High efficiency, high output current

**Technical Approach**:

Optimal dead time control to improve efficiency

□ Latest Results:

Feasibility study of single-stage high voltage conversion



